

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
85V	4mΩ@10V	125A

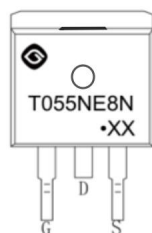
Feature

- Split Gate Trench Technology
- Low $R_{DS(on)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Industrial Power Supply
- Load Switch

MARKING



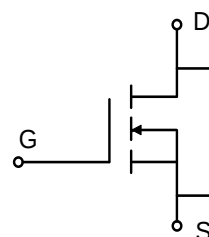
T055NE8N = Device Code
XX = Date Code
Solid Dot = Green Indicator

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TO-263-2L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	85	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current ¹	I_D	125	A
Pulsed Drain Current ²	I_{DM}	500	A
Single Pulsed Avalanche Current ³	I_{AS}	47	A
Single Pulsed Avalanche Energy ³	E_{AS}	552	mJ
Power Dissipation ⁵	P_D	162	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	58	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.77	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

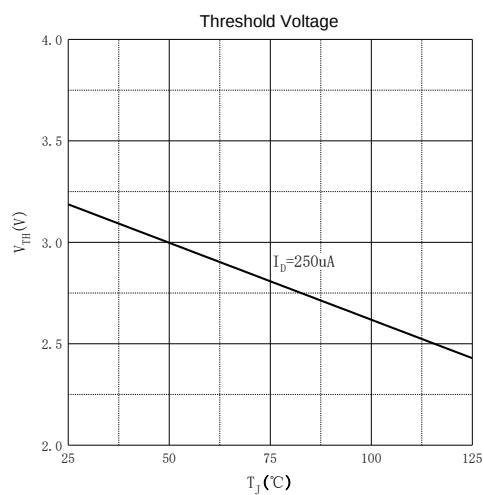
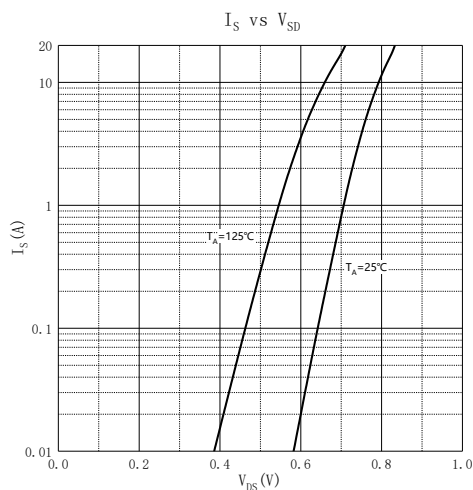
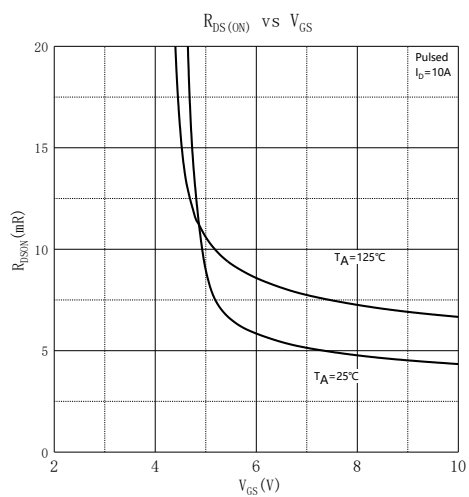
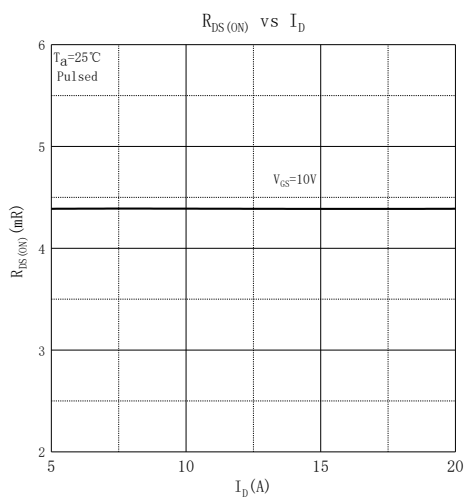
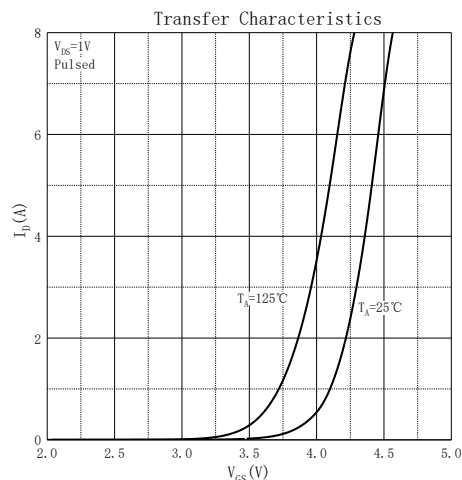
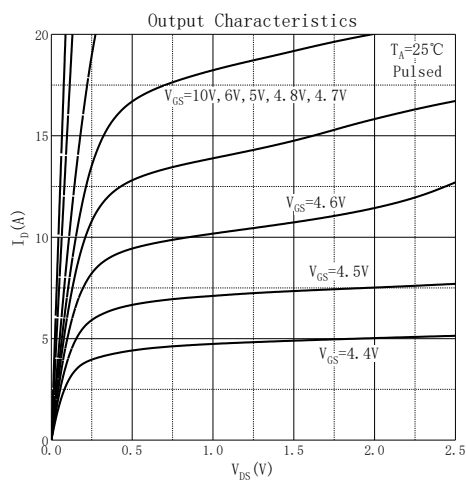
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

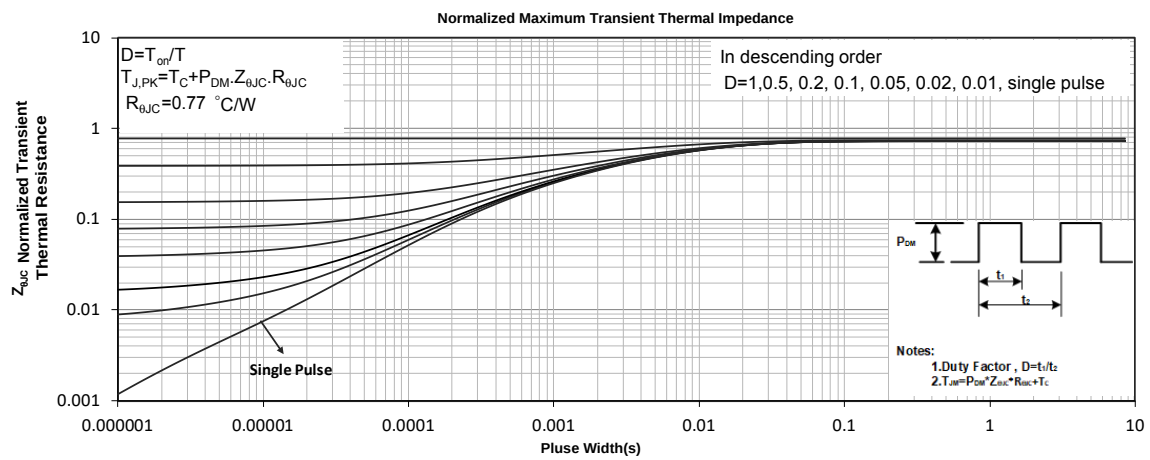
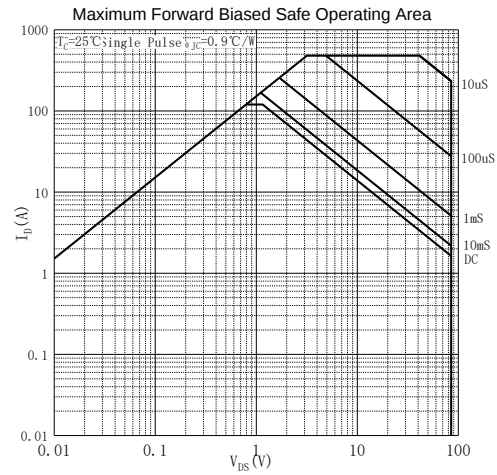
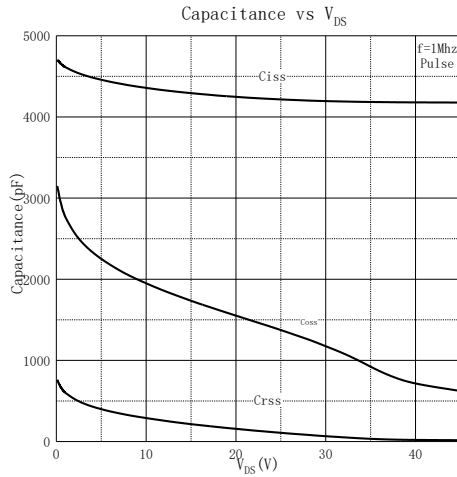
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	85			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics ⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$		4	5.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 10A$	60			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 40V, V_{GS} = 0V, f = 1MHz$		4274		pF
Output Capacitance	C_{oss}			655		
Reverse Transfer Capacitance	C_{rss}			28		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.6		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 45V, V_{GS} = 10V, I_D = 20A$		60		nC
Gate-source Charge	Q_{gs}			28		
Gate-drain Charge	Q_{gd}			17		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 45V, V_{GS} = 10V, R_L = 2\Omega$ $R_G = 3\Omega$		25		ns
Turn-on Rise Time	t_r			21		
Turn-off Delay Time	$t_{d(off)}$			53		
Turn-off Fall Time	t_f			24		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 10A$	0.5		1.4	V

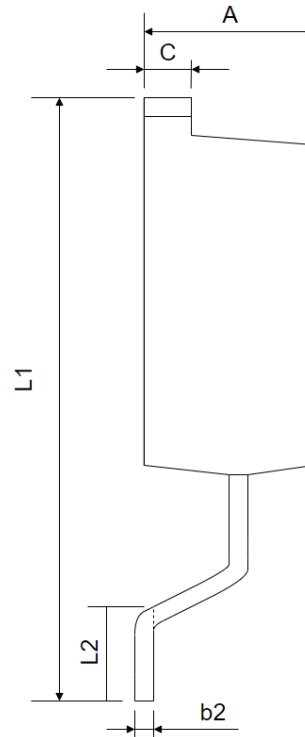
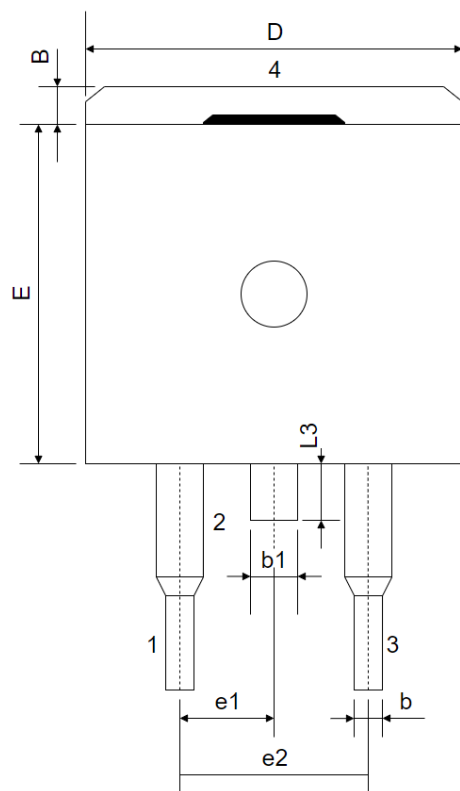
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 25V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics





TO-263-2L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
B	1.000	1.400	0.039	0.055
b	0.700	0.900	0.028	0.035
b1	1.150	1.350	0.045	0.053
b2	0.400	0.600	0.016	0.024
C	1.200	1.400	0.047	0.055
D	9.800	10.200	0.386	0.402
E	9.000	9.400	0.354	0.370
e1	2.340	2.740	0.092	0.108
e2	4.880	5.280	0.192	0.208
L1	15.000	16.000	0.591	0.630
L2	2.240	2.840	0.088	0.112
L3	1.200	1.600	0.047	0.063